

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Group : 1763  
Applicant : Imad Mahawili, PhD  
Serial No. : 09/488,309  
Filed : January 20, 2000  
For : REACTOR WITH REMOTE PLASMA SYSTEM AND  
METHOD OF PROCESSING A SEMICONDUCTOR  
SUBSTRATE

Official  
FAX RECEIVED  
MAY 18 2001  
GROUP 1700

Commissioner for Patents  
Washington, D.C. 20231

Dear Sir:

SECOND PRELIMINARY AMENDMENT

Prior to examination, Applicant wishes to his application as follows:

IN THE CLAIMS:

Please add new claims.

72. (New)

A substrate processing apparatus comprising:

a processing chamber; and

a gas injection assembly for injecting at least one gas into said processing

B1  
chamber and being adapted to make the gas injected into said processing chamber into a gas plasma, wherein said gas injection assembly includes at least two gas injection tubes, a first of said gas injection tubes injecting a first gas in said processing chamber, a second of said gas injection tubes injecting a second gas in said processing chamber, and said gas injection assembly making at least one of said first and second gases into the gas plasma for injecting into said processing chamber.

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5/21/91  
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